



YEA SHIN TECHNOLOGY CO., LTD

YSCLAMP3611P

Low Capacitance Bidirectional Mocro Packaged TVS Diodes for ESD Protection



Features

- Peak Power Dissipation –200W (8 x 20 us Waveform)
- Stand-off Voltage: 36V
- Protects I/O or Power Port
- Low Clamping Voltage
- Low Leakage
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- ROHS compliant
- Solid-state TVS Process technology

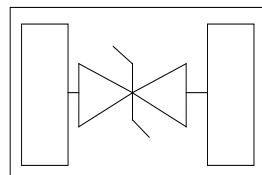
DFN1006



Main applications

- LED Drive Line
- Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Projection TV
- Cellular handsets and accessories
- Portable instrumentation
- MP3 Players

PIN CONFIGURATION



Protection solution to meet

- IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC61000-4-5 (Lightning) 2.5A (8/20μs)

Marking : T6

Ordering Information

Device	Qty per Reel	Reel Size
YSCLAMP3611P	10000 / Tape & Reel	7 Inch

DEVICE CHARACTERISTICS

YSCLAMP3611P

Maximum ratings (Tamb=25°C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform) (Note 1)	P _{PPP}	200	Watts
ESD Rating per IEC61000-4-2:	Contact	8	KV
	Air	15	
Lead Soldering Temperature	T _L	260 (10 sec.)	°C
Operating Temperature Range	T _J	-55 ~ 150	°C
Storage Temperature Range	T _{STG}	-55 ~ 150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T _L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

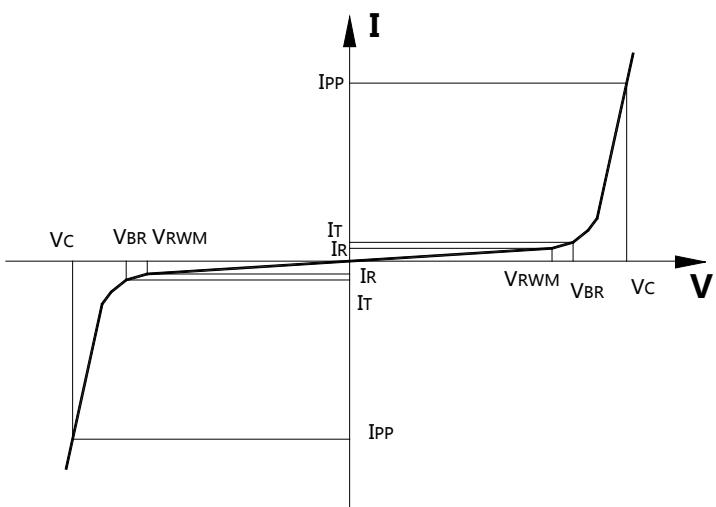
*Other voltages may be available upon request.

Note : 1. Non-repetitive current pulse, per Figure 1.

Electrical characteristics (Tamb=25°C Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V _{RWM}	Reverse Working Voltage				36	V
V _{BR}	Reverse Breakdown Voltage	IT = 1mA,	40			V
I _R	Reverse Leakage Current	V _{RWM} = 36V,		0.05	1	μA
V _C	Clamping Voltage	I _{PP} = 1A, tp =8/20μs,			65	V
		I _{PP} =2.5A, tp =8/20μs,		80	110	V
C _J	Junction Capacitance	V _R = 0V, f = 1MHz,		14	25	pF

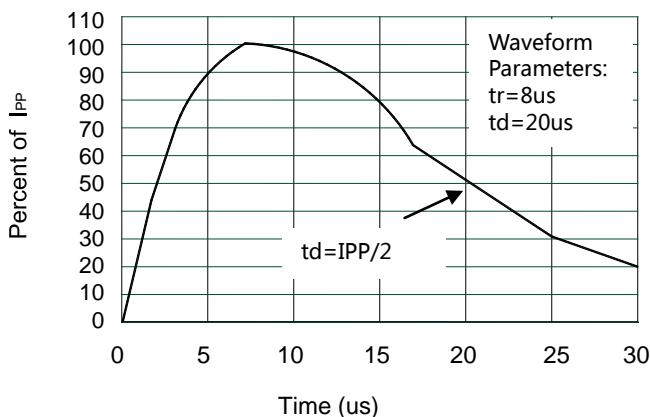
Symbol	Parameter
V _{RWM}	Working Peak Reverse Voltage
V _{BR}	Breakdown Voltage @ I _T
V _C	Clamping Voltage @ I _{PP}
I _T	Test Current
I _{RM}	Leakage current at V _{RWM}
I _{PP}	Peak pulse current
C _O	Off-state Capacitance
C _J	Junction Capacitance



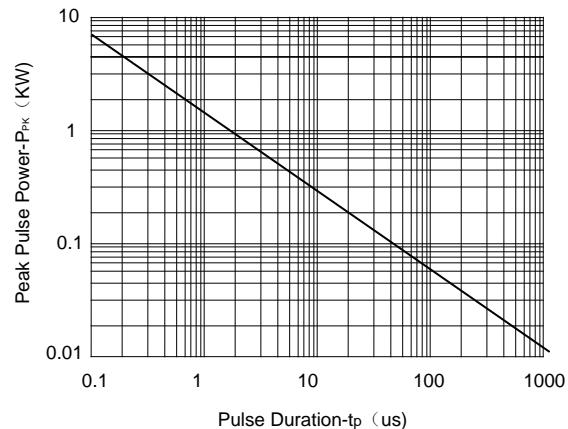
DEVICE CHARACTERISTICS

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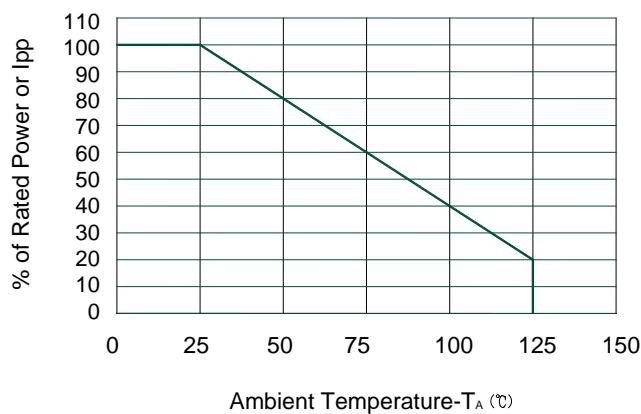
Typical electrical characterist applications



Pulse Waveform



Non-Repetitive Peak Pulse Power vs. Pulse Time



Power Derating Curve

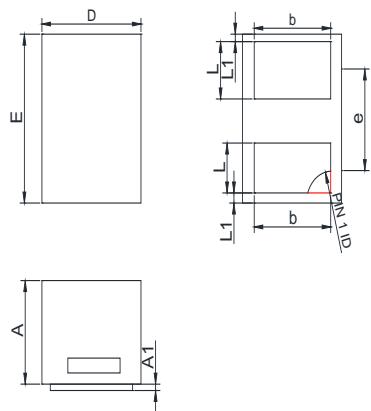
PACKAGE OUTLINE & DIMENSIONS

YSCLAMP3611P

Mechanical Data

Case:DFN1006

Case Material: Molded Plastic. UL Flammability



DIM	Millimeters	
	Min	Max
A	0.30	0.50
A1	0.00	0.05
D	0.55	0.65
E	0.95	1.05
b	0.25	0.60
e	0.65TYP	
L	0.15	0.35
L1	0.05REF	